Santa Barbara 2005

1/21/2005

Spin susceptibility near metal-insulator transition in 2D

Sveta Anissimova

Alexander Shashkin

Mohammed Sakr (now at UCLA)



Sergey Kravchenko (presenting author

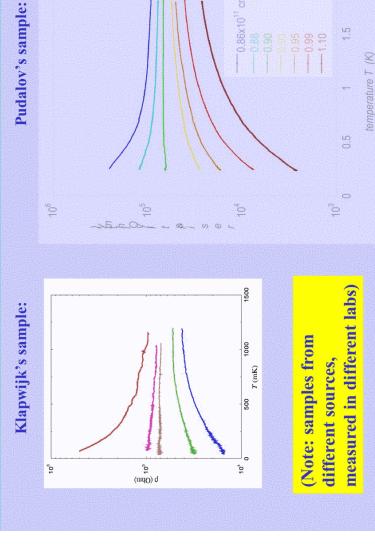
Valeri Dolgopolov

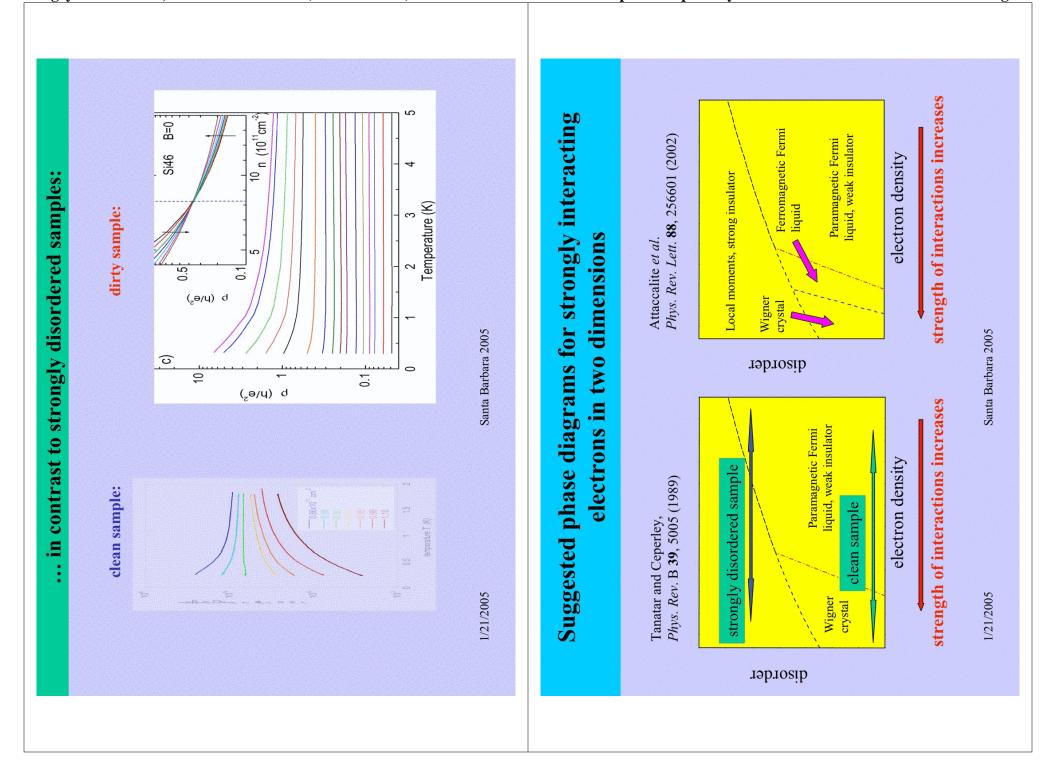
Teun Klapwijk

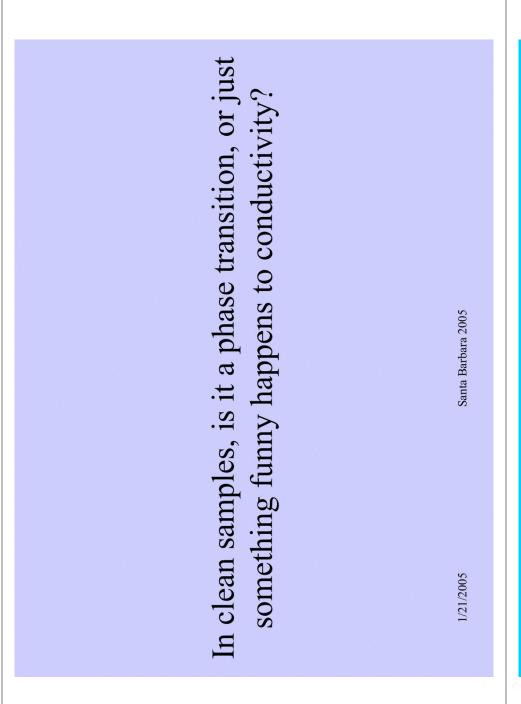
1/21/2005

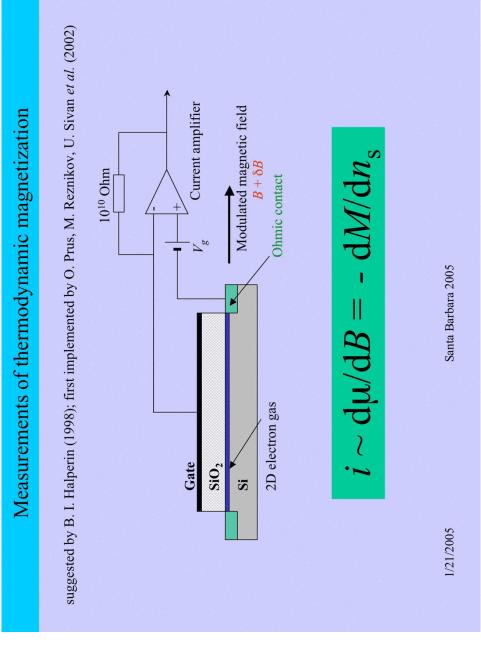
Santa Barbara 2005

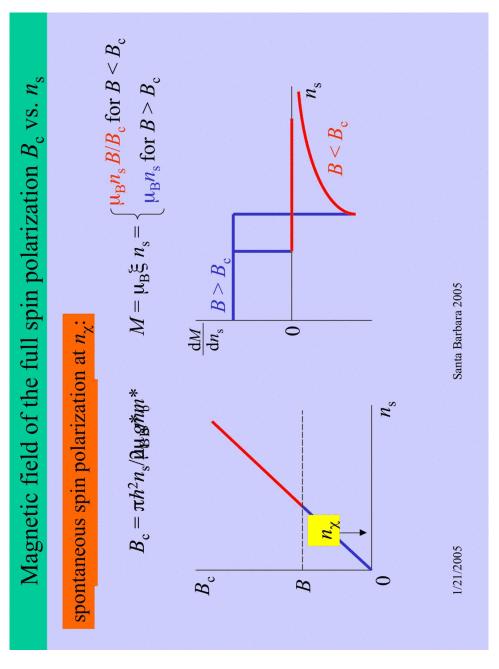
In very clean samples, practically universal metal-insulator transition is seen:

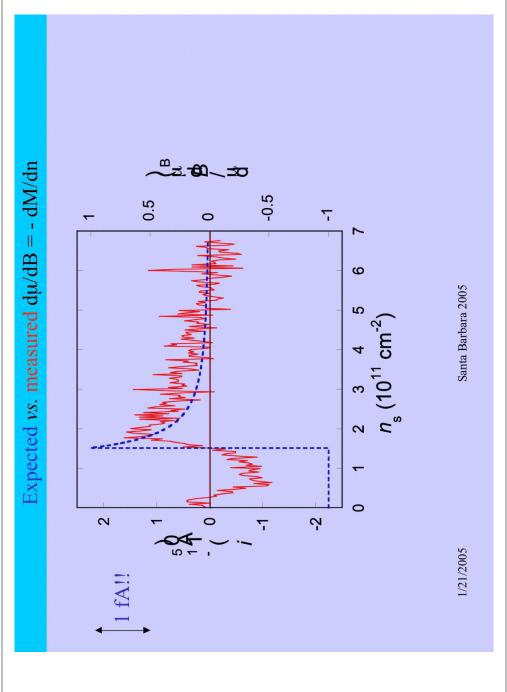


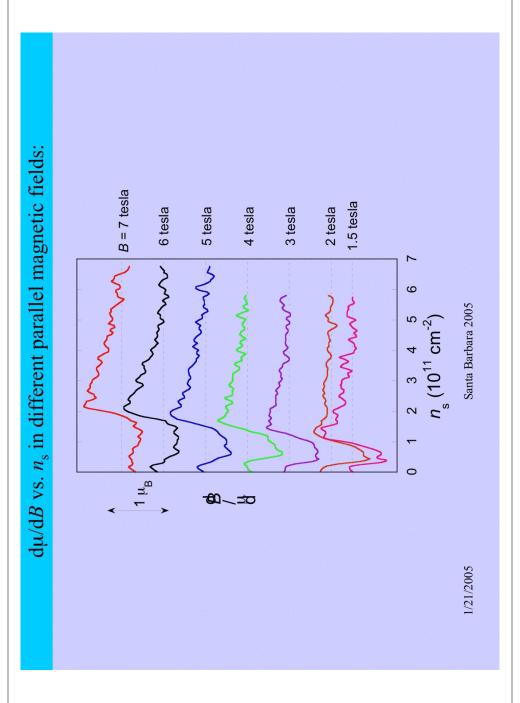


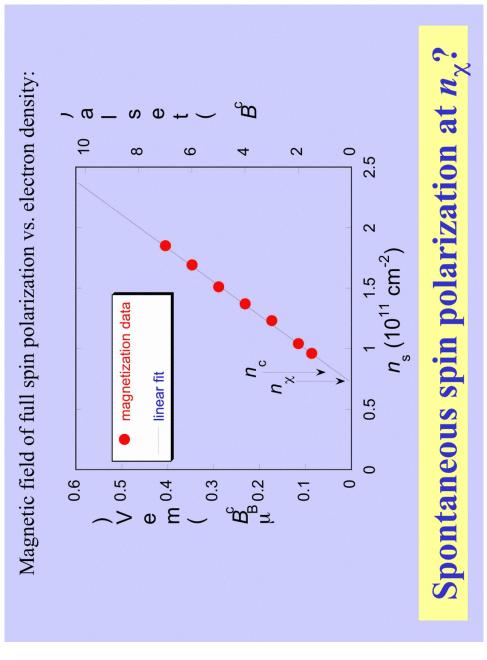


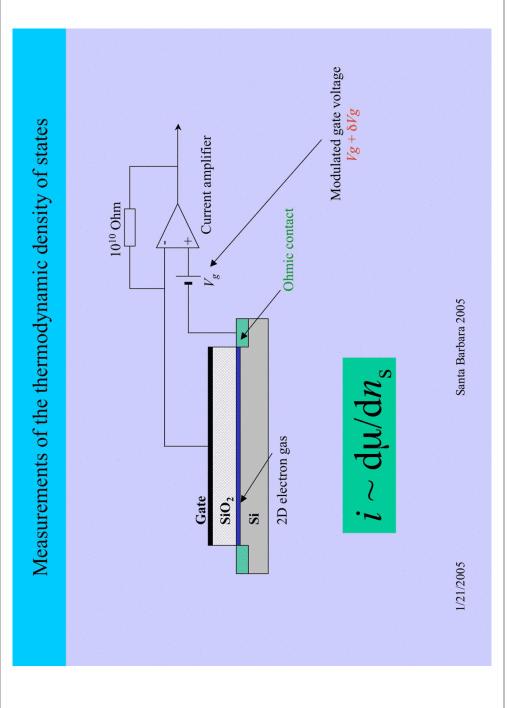


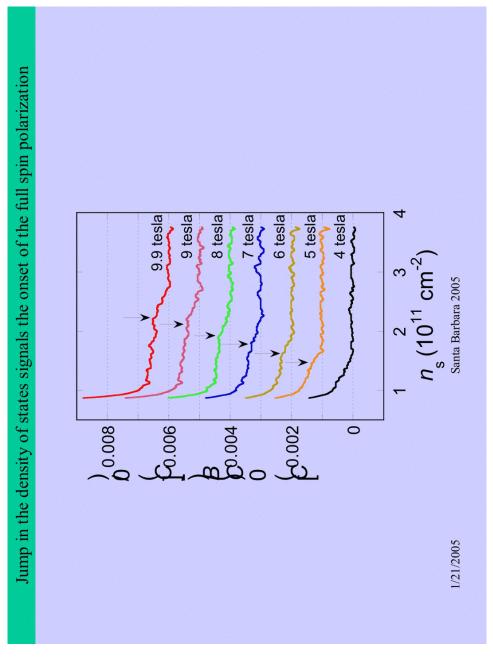


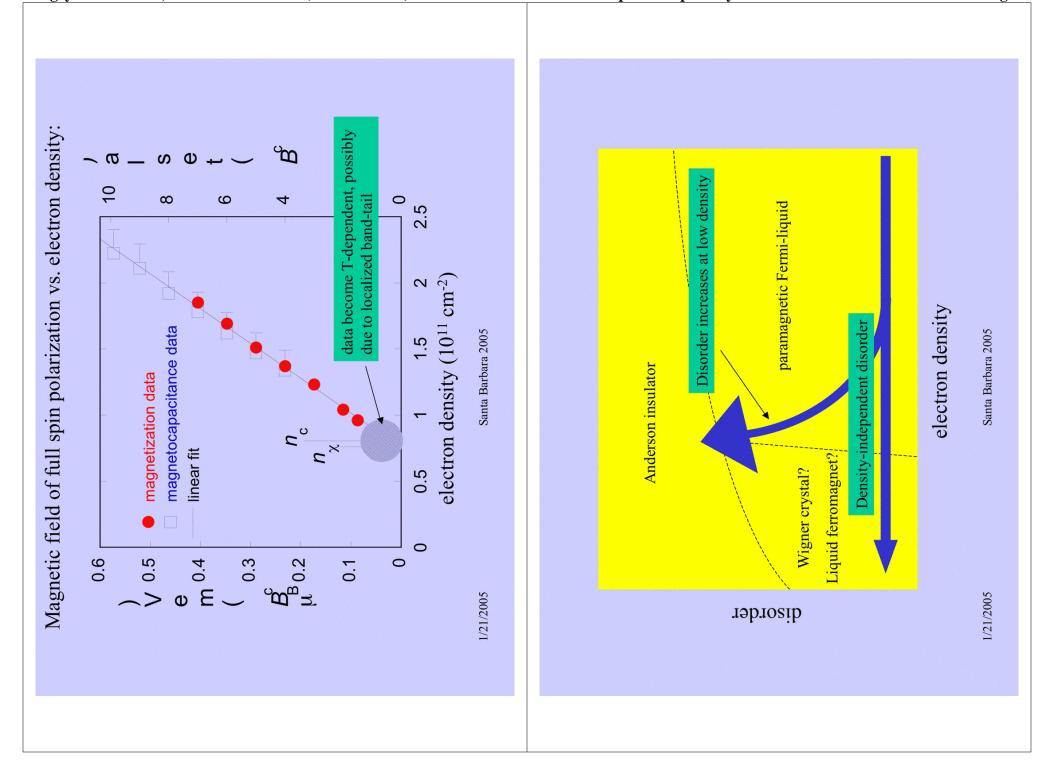


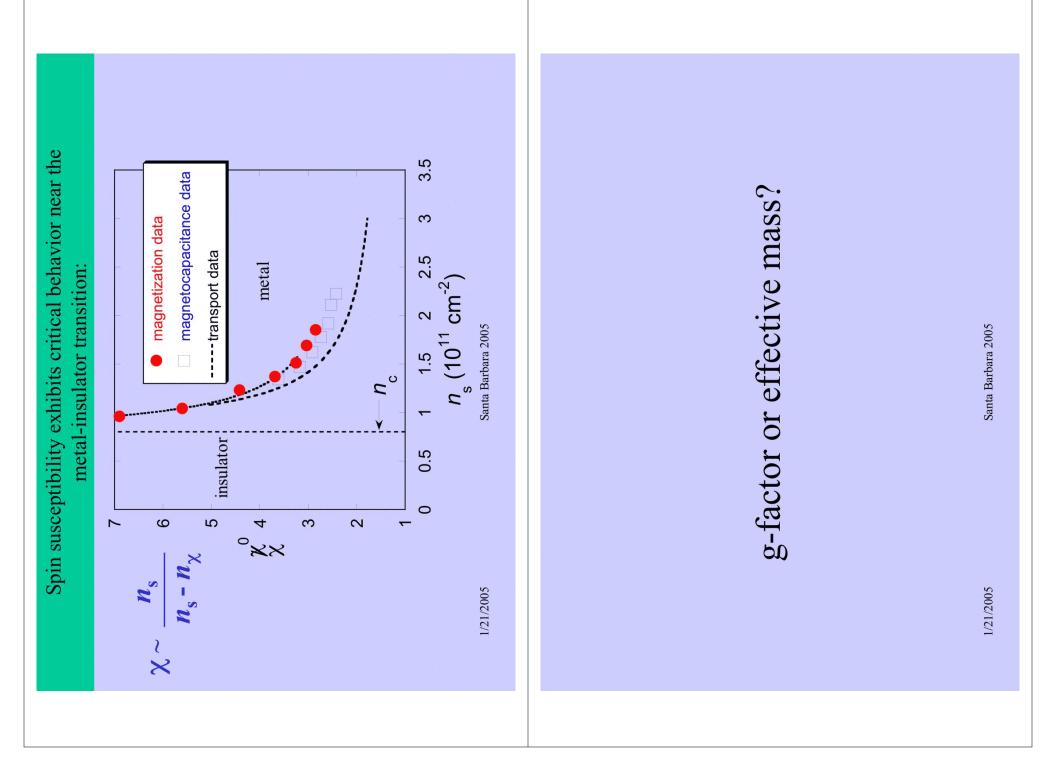


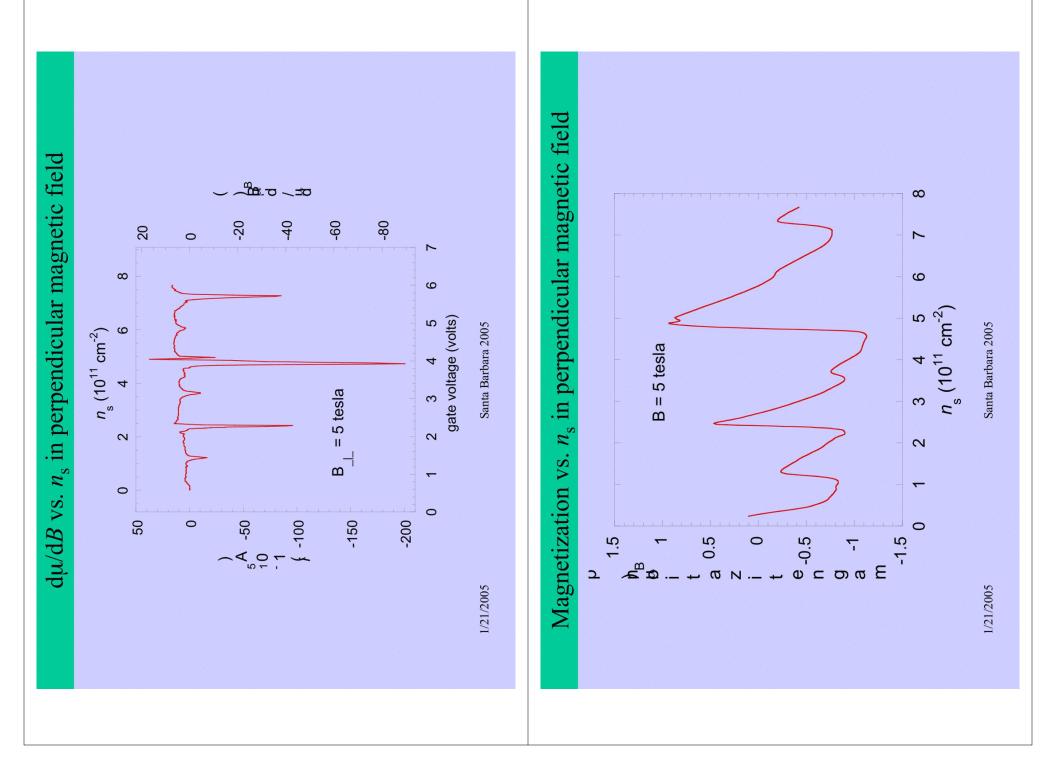


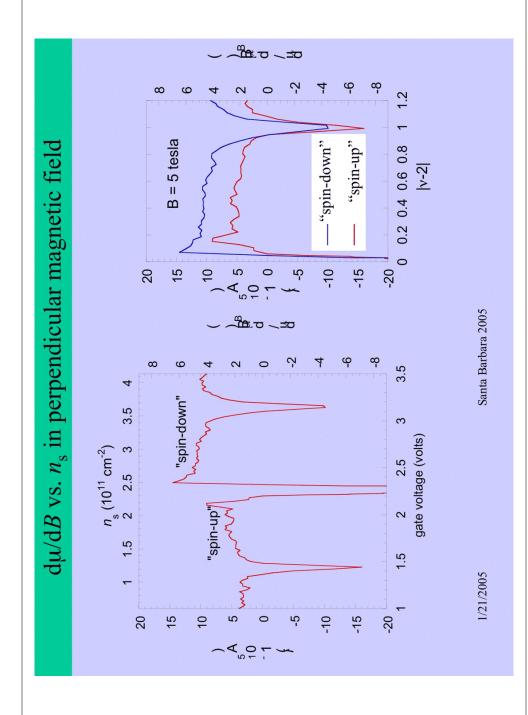


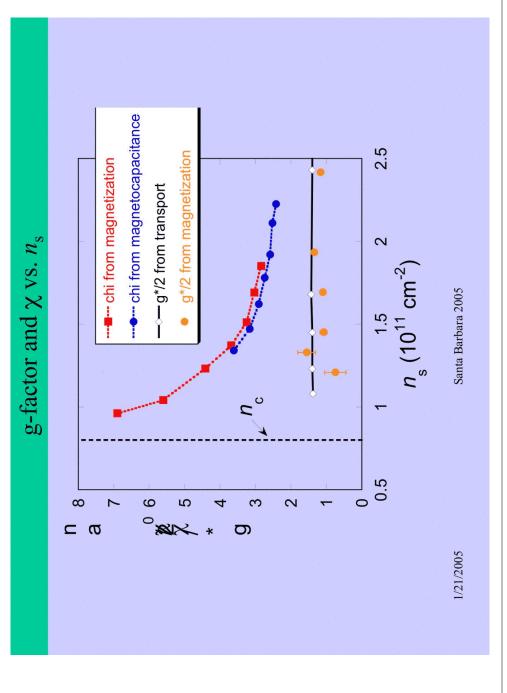












CONCLUSIONS

susceptibility sharply rises with a tendency to diverge at a sample-In strongly interacting 2D electron system in silicon, spin independent density n_{χ} .

• We find no evidence of increasing g-factor: it must be the effective mass that is responsible for the effect

• In clean samples, n_{χ} practically = coincides with the metal-insulator transition.

Santa Barbara 2005

1/21/2005

103

